T事识"iST651sM"供应商

BT151S series BT151M series

GENERAL DESCRIPTION

Glass passivated thyristors in a plastic envelope, suitable surface for mounting, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

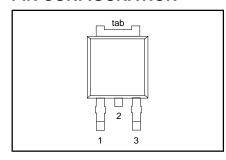
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} , V _{RRM} I _{T(AV)} I _{T(RMS)} I _{TSM}	BT151S (or BT151M)- Repetitive peak off-state voltages Average on-state current RMS on-state current Non-repetitive peak on-state current	500R 500 7.5 12 100	650R 650 7.5 12 100	800R 800 7.5 12 100	V A A A

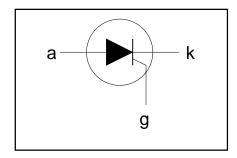
PINNING - SOT428

PIN NUMBER	Standard S	Alternative M
1	cathode	gate
2	anode	anode
3	gate	cathode
tab	anode	anode

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	. MAX.		UNIT	
V_{DRM} , V_{RRM}	Repetitive peak off-state voltages		-	-500R 500 ¹	-650R 650 ¹	-800R 800	>
I _{T(AV)} I _{T(RMS)} I _{TSM}	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{mb} \le 103$ °C all conduction angles half sine wave; $T_j = 25$ °C prior to surge	-		7.5 12		A A
		t = 10 ms t = 8.3 ms	-		100 110		A A
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after triggering	t = 10 ms $I_{TM} = 20 \text{ A}; I_{G} = 50 \text{ mA};$ $dI_{G}/dt = 50 \text{ mA/}\mu\text{s}$	-		50 50		A²s A/μs
I _{GM} V _{GM} V _{RGM}	Peak gate current Peak gate voltage Peak reverse gate voltage Peak gate power		-		2 5 5 5		A V V W
P _{GM} P _{G(AV)} T _{stg} T _j	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	-40 -		0.5 150 125		≎ېې

September 1997 1 Rev 1.100

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/μs.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}	Thermal resistance		-	-	1.8	K/W
R _{th j-a}	junction to mounting base Thermal resistance junction to ambient	pcb (FR4) mounted; footprint as in Fig.14	-	75	-	K/W

STATIC CHARACTERISTICS

 $T_j = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	2	15	mΑ
l IĽ	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	10	40	mΑ
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	7	20	mΑ
Ϊ́Τ	On-state voltage	$I_{T} = 23 \text{ A}$	-	1.4	1.75	V
V _{GT}	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.6	1.5	V
		$V_D = V_{DRM(max)}$; $I_T = 0.1 \text{ A}$; $T_j = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
I_D, I_R	Off-state leakage current	$V_D = V_{DRM(max)}$; $V_R = V_{RRM(max)}$; $T_j = 125$ °C	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}$; $T_j = 125 ^{\circ}C$; exponential waveform; Gate open circuit	50	130	_	V/us
		$R_{GK} = 100 \Omega$	200	1000	_	V/μs
$\mathbf{t}_{ ext{gt}}$	Gate controlled turn-on time	$I_{TM} = 40 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs
t _q	Circuit commutated turn-off time	$V_D = 67\% \ V_{DRM(max)}$; $T_j = 125 \ ^{\circ}C$; $I_{TM} = 20 \ A$; $V_R = 25 \ V$; $dI_{TM}/dt = 30 \ A/\mu s$; $dV_D/dt = 50 \ V/\mu s$; $R_{GK} = 100 \ \Omega$	-	70	-	μs

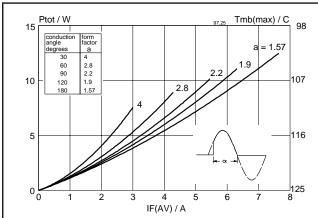


Fig.1. Maximum on-state dissipation, P_{tot} versus average on-state current, $I_{T(AV)}$, where $a = form \ factor = I_{T(RMS)} / I_{T(AV)}$

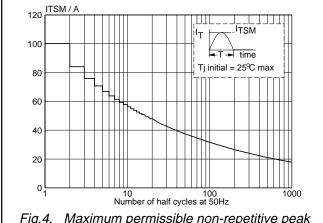


Fig.4. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus number of cycles, for sinusoidal currents, f = 50 Hz.

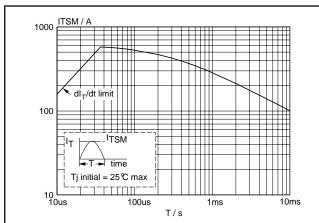


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 10$ ms.

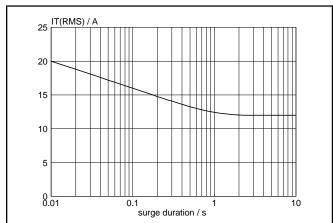


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 103$ °C.

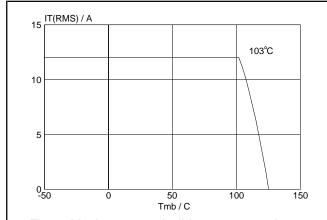


Fig.3. Maximum permissible rms current I_{T(RMS)}, versus mounting base temperature T_{mb} .

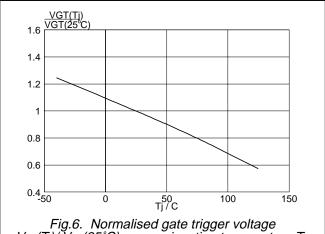
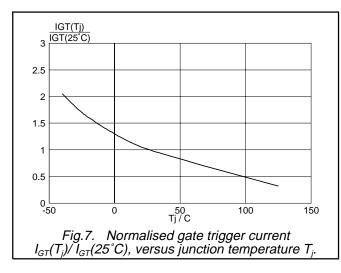
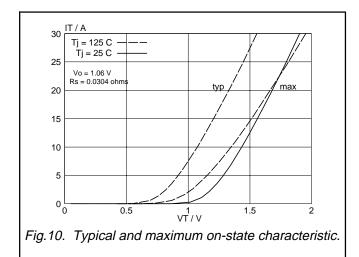
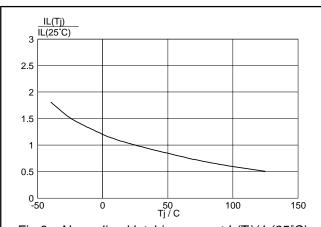


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature $T_{j^{\circ}}$







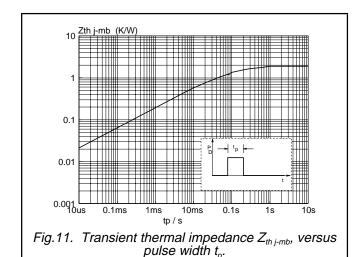
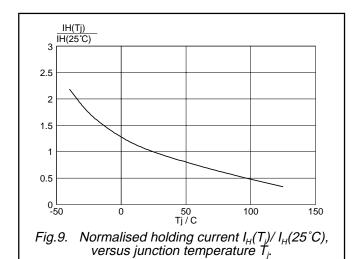


Fig.8. Normalised latching current $I_L(T_i)/I_L(25^{\circ}C)$, versus junction temperature T_i



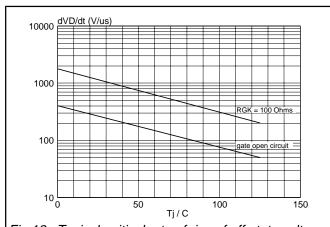
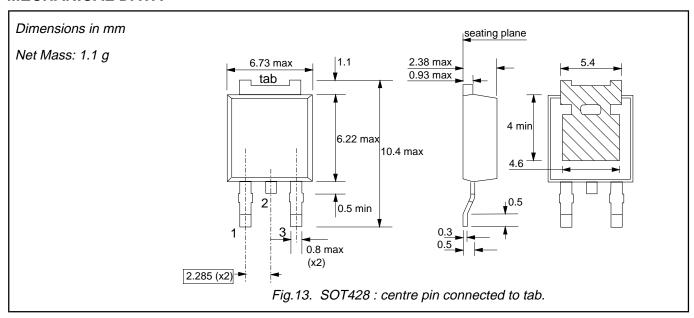
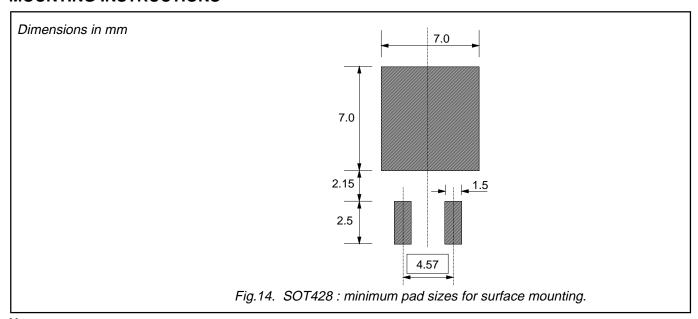


Fig.12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_j.

MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

1. Plastic meets UL94 V0 at 1/8".

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BT151M series

DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				
Limitim muncles o					

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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